

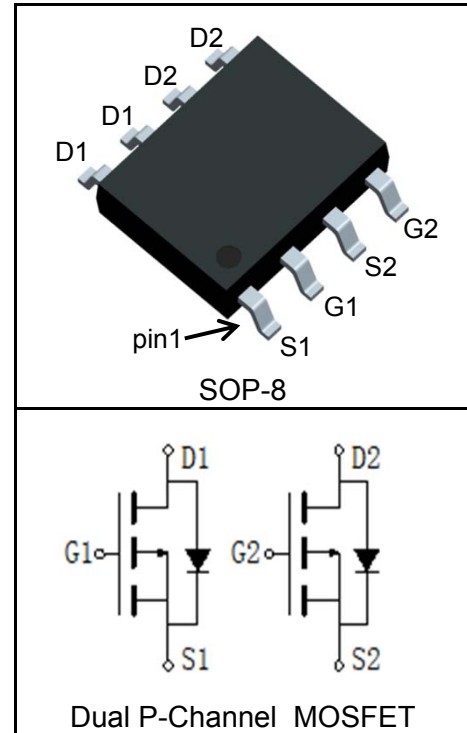
Features

- -30V/-15A,
 $R_{DS(ON)} = 15m\Omega(Typ.)@V_{GS}=-10V$
 $R_{DS(ON)} = 22m\Omega(Typ.)@V_{GS}=-4.5V$
- Low On-Resistance
- Super High Dense Cell Design
- Reliable and Rugged
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Power management
- Load switch
- Battery protection

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	-30	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	150	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_A=25^\circ\text{C}$ -8	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_A=25^\circ\text{C}$ -60	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=-10V$)	$T_A=25^\circ\text{C}$ -15	A
		$T_A=70^\circ\text{C}$ -12	
P_D	Maximum Power Dissipation	$T_A=25^\circ\text{C}$ 2.5	W
		$T_A=70^\circ\text{C}$ 1.6	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	-	$^\circ\text{C}/\text{W}$
$R_{\theta JA}^{③}$	Thermal Resistance-Junction to Ambient	50	$^\circ\text{C}/\text{W}$
Drain-Source Avalanche Ratings			
$E_{AS}^{④}$	Avalanche Energy, Single Pulsed	-	mJ

Electrical Characteristics ($T_A=25^\circ\text{C}$ Unless Otherwise Noted)

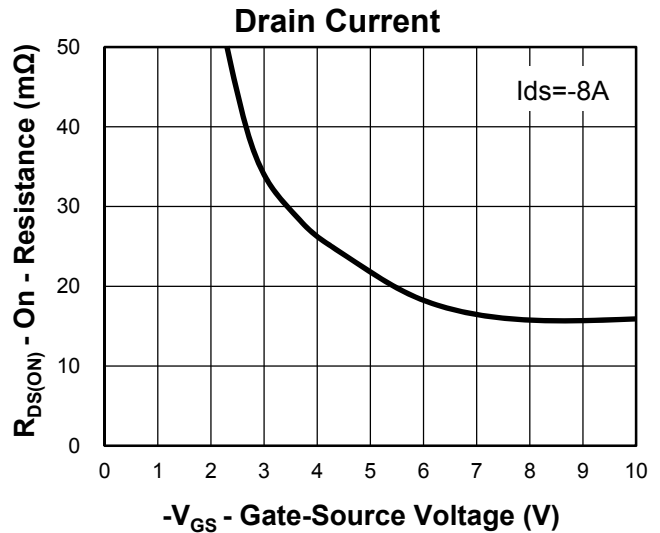
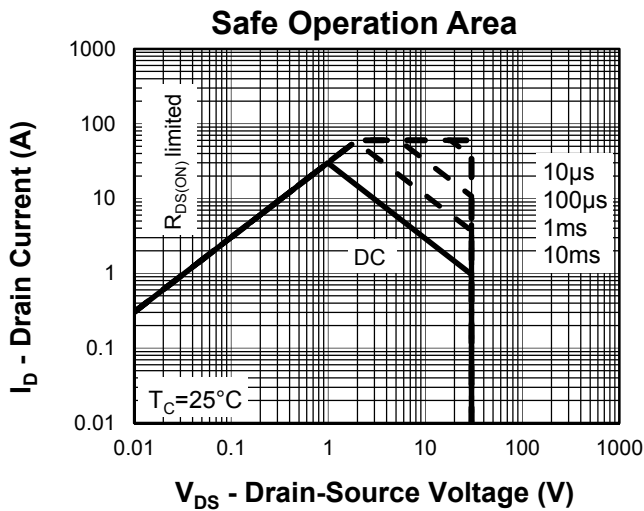
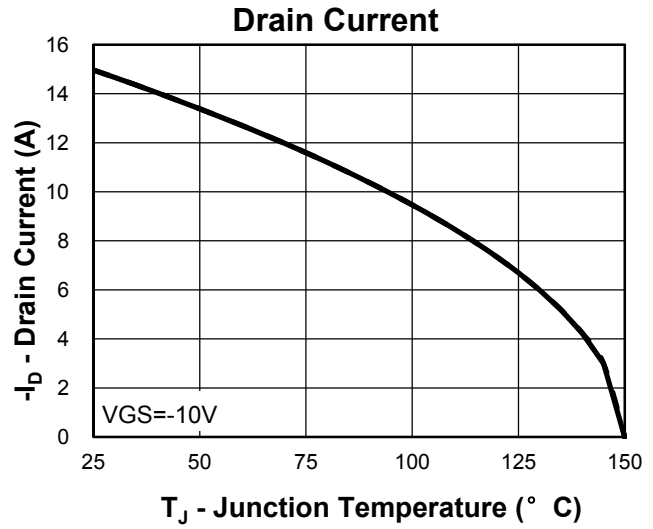
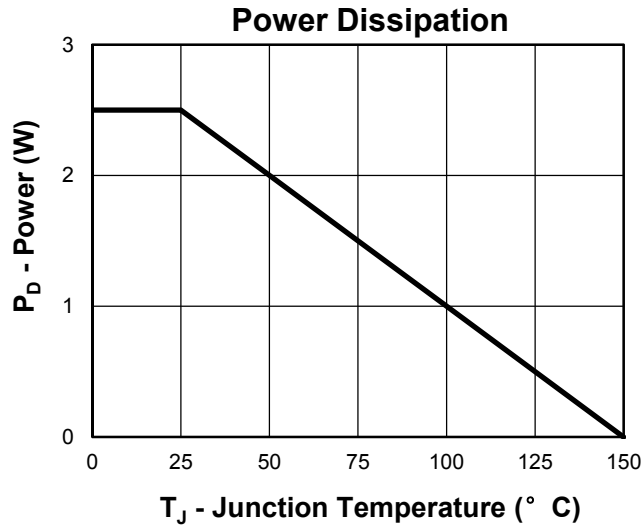
Symbol	Parameter	Test Condition	RU30S15H			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=-250\mu A$	-30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V$			-1	μA
		$T_J=125^\circ C$			-30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=-250\mu A$	-1		-2.5	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(5)}$	Drain-Source On-state Resistance	$V_{GS}=-10V, I_{DS}=-8A$		15	18	$m\Omega$
		$V_{GS}=-4.5V, I_{DS}=-6A$		22	26	$m\Omega$
Diode Characteristics						
$V_{SD}^{(5)}$	Diode Forward Voltage	$I_{SD}=-8A, V_{GS}=0V$			-1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=-15A, dI_{SD}/dt=100A/\mu s$		45		ns
Q_{rr}	Reverse Recovery Charge			26		nC
Dynamic Characteristics ⁽⁶⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.8		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=-15V,$ Frequency=1.0MHz		2300		pF
C_{oss}	Output Capacitance			250		
C_{rss}	Reverse Transfer Capacitance			160		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=-15V, R_L=3\Omega,$ $I_{DS}=-15A, V_{GEN}=-10V,$ $R_G=6\Omega$		17		ns
t_r	Turn-on Rise Time			32		
$t_{d(OFF)}$	Turn-off Delay Time			37		
t_f	Turn-off Fall Time			15		
Gate Charge Characteristics ⁽⁶⁾						
Q_g	Total Gate Charge	$V_{DS}=-24V, V_{GS}=-10V,$ $I_{DS}=-15A$		42		nC
Q_{gs}	Gate-Source Charge			9		
Q_{gd}	Gate-Drain Charge			13		

- Notes:
- ① Pulse width limited by safe operating area.
 - ② Calculated continuous current based on maximum allowable junction temperature.
 - ③ When mounted on 1 inch square copper board, $t \leq 10\text{sec}$. The value in any given application depends on the user's specific board design.
 - ④ Limited by T_{Jmax} . Starting $T_J = 25^\circ\text{C}$.
 - ⑤ Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑥ Guaranteed by design, not subject to production testing.

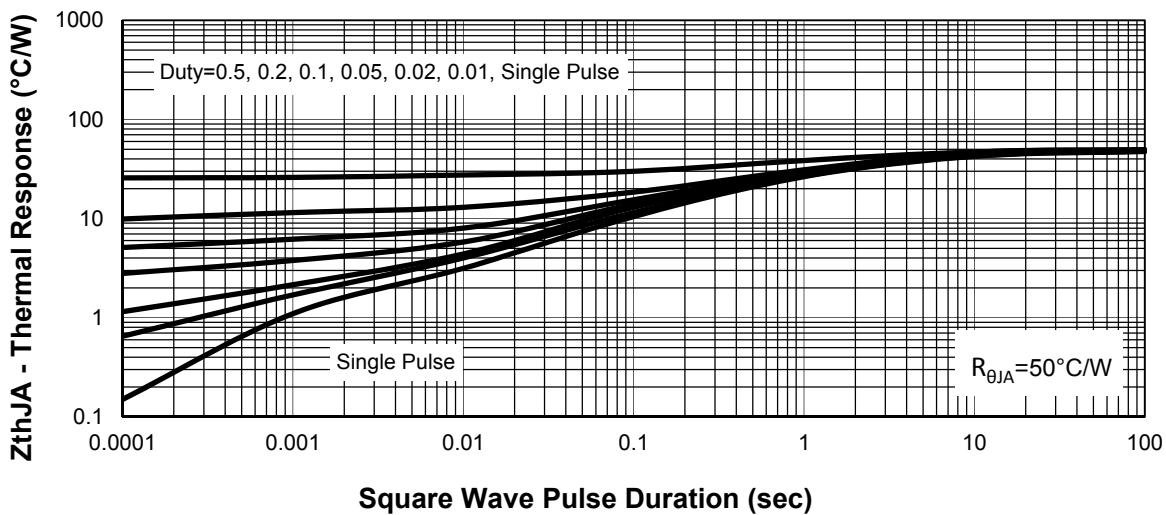
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU30S15H	RU30S15H	SOP-8	Tape&Reel	2500	13"	12mm

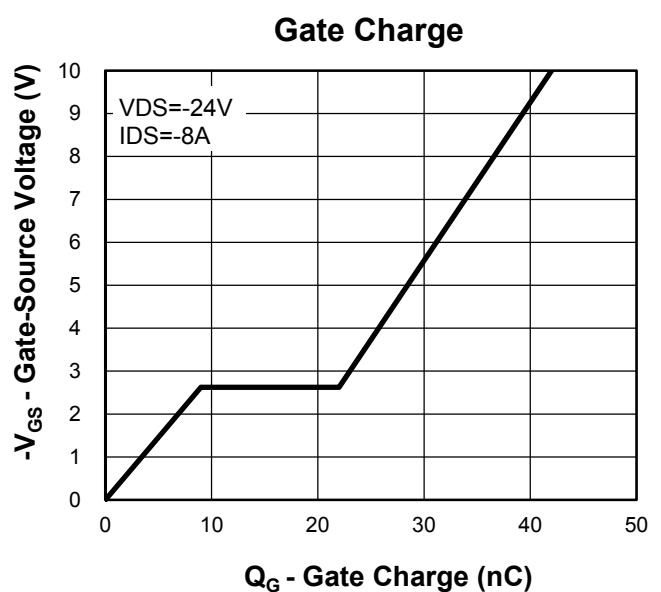
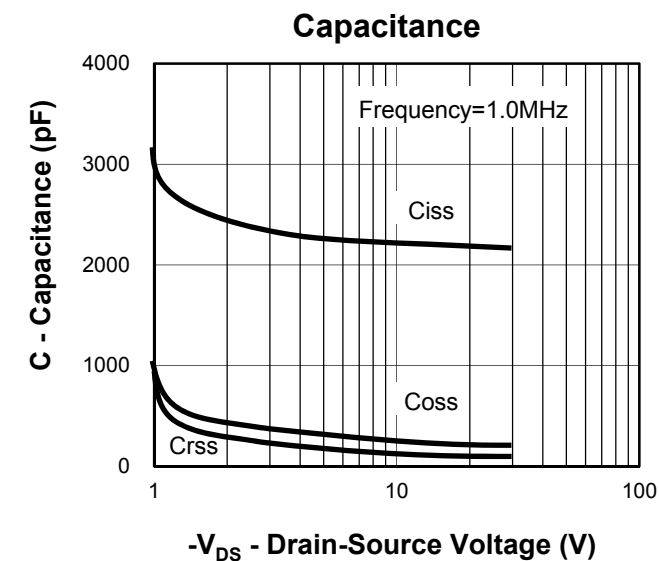
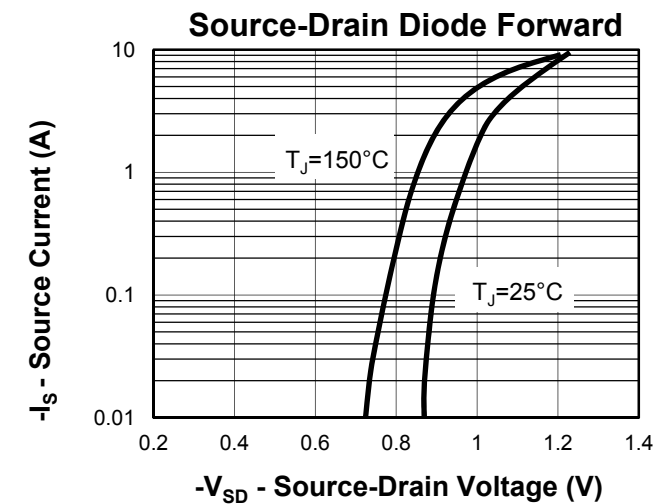
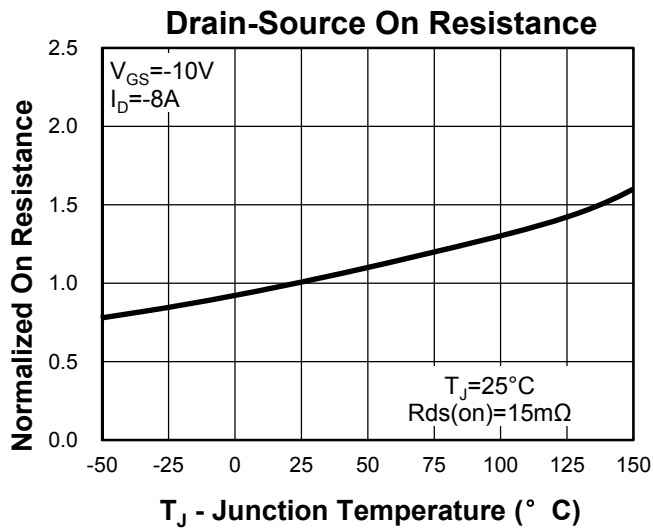
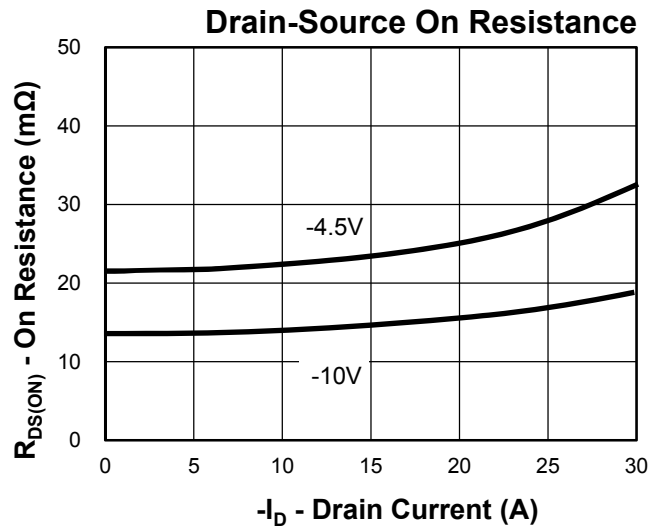
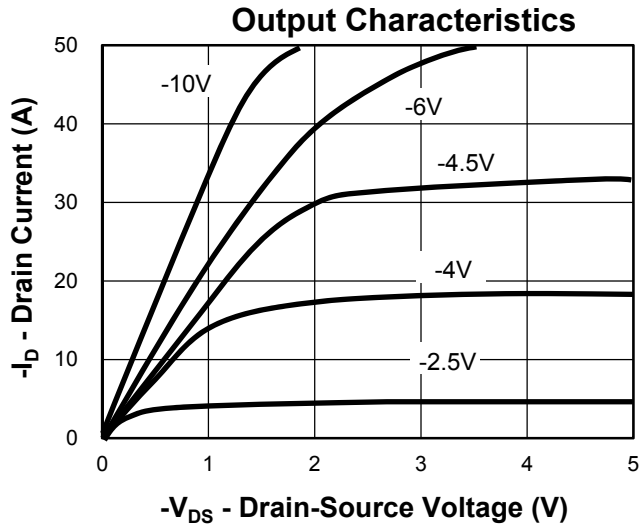
Typical Characteristics



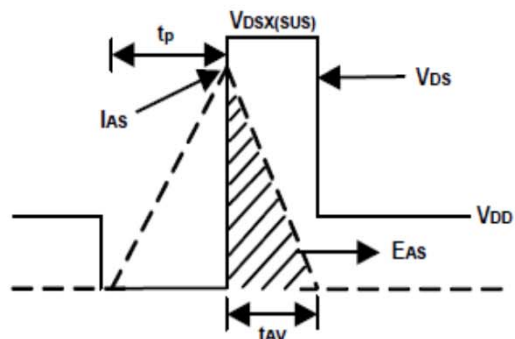
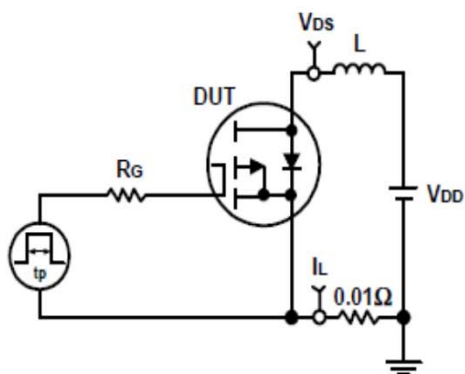
Thermal Transient Impedance



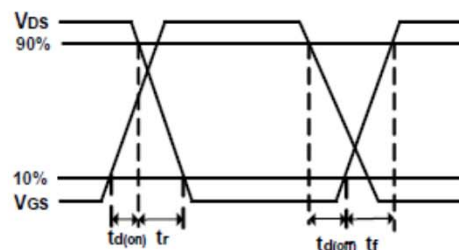
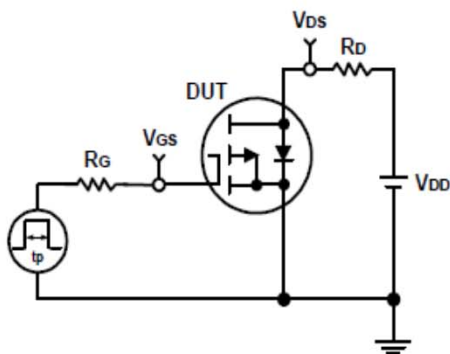
Typical Characteristics



Avalanche Test Circuit and Waveforms

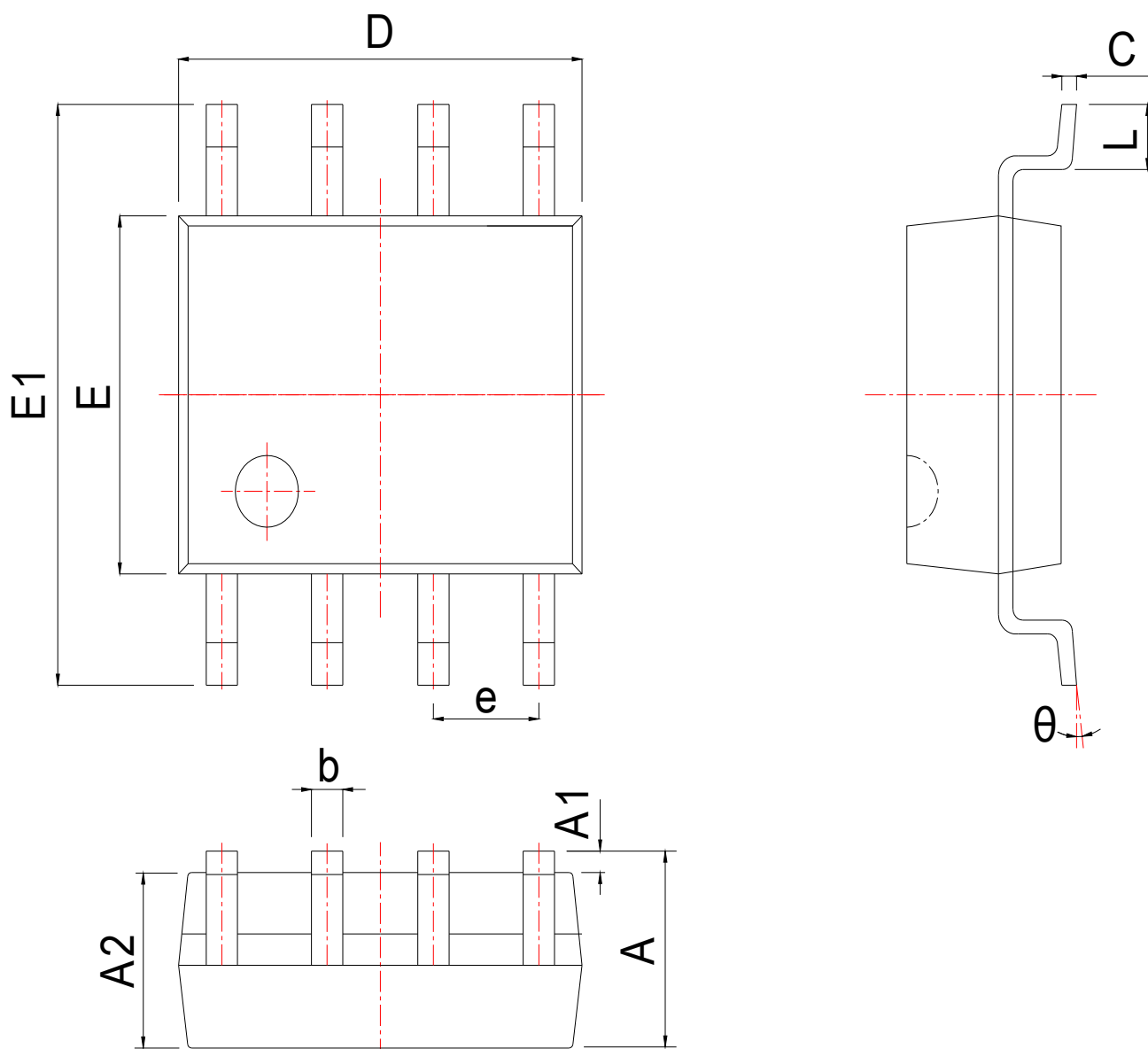


Switching Time Test Circuit and Waveforms



Package Information

SOP-8



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.300	1.525	1.750	0.051	0.060	0.069
A1	0.050	0.150	0.250	0.002	0.006	0.010
A2	1.350	1.450	1.550	0.053	0.057	0.061
b	0.330	0.420	0.510	0.013	0.017	0.020
c	0.170	0.210	0.250	0.007	0.008	0.010
D	4.700	4.900	5.100	0.185	0.193	0.201
E	3.800	3.900	4.000	0.150	0.154	0.157
E1	5.800	6.000	6.200	0.228	0.236	0.244
e	1.270 BSC			0.050 BSC		
L	0.400	0.835	1.270	0.016	0.033	0.050
θ	0°		8°	0°		8°

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